

L Number	Hits	Search Text	DB	Time stamp
1	1	("6563216").PN.	USPAT	2004/09/06 06:40
2	688	257/499	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
3	531	257/500	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
5	370	257/501	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
6	189	257/502	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
7	327	257/503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
8	82	257/504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:40
9	1774	257/499 257/500 257/501 257/502 257/503 257/504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:41
10	1131	(257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:41
11	690	((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:41
12	101	((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and cell and peripheral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:51
13	299723	257/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:51
17	130	((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and memory and peripher\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:51
18	16446	257/\$ and memory and peripher\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:52

19	1305	(257/\$ and memory and peripher\$) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:52
20	642	((257/\$ and memory and peripher\$) and (aspect adj ratio)) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:52
21	606	((257/\$ and memory and peripher\$) and (aspect adj ratio)) and trench) and (oxide or dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:53
22	589	((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) not (((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and cell and peripheral)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 06:53
23	418	((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) not (((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and cell and peripheral)) and (width or depth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:06
24	3007	257/\$ and (trench near2 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:07
25	1583	(257/\$ and (trench near2 width)) and (trench near3 depth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:07
26	1449	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:07
27	1498	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:07
28	0	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and peripher	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:08
29	219	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and peripher\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 07:39
30	1279	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) not (((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and peripher\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 08:17
31	2	("6642125").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 08:17